

ABSTRACT

A method and apparatus for sensing a state of a memory circuit, in particular a content address memory (CAM) device are described. The method includes receiving a first current signal as an input, the first current signal corresponding to a state of the memory circuit, converting the first current signal into a first voltage signal, converting the first voltage signal into a second voltage signal and sensing the second voltage signal. The apparatus includes an input adapted to receive a first current signal, the first current signal corresponding to the state of the memory circuit; and a current mirror circuit having a first portion adapted to receive the first current signal and convert the first current signal to a first voltage signal and a second portion adapted to receive the first voltage signal and convert the first voltage signal into a second voltage signal as an output.